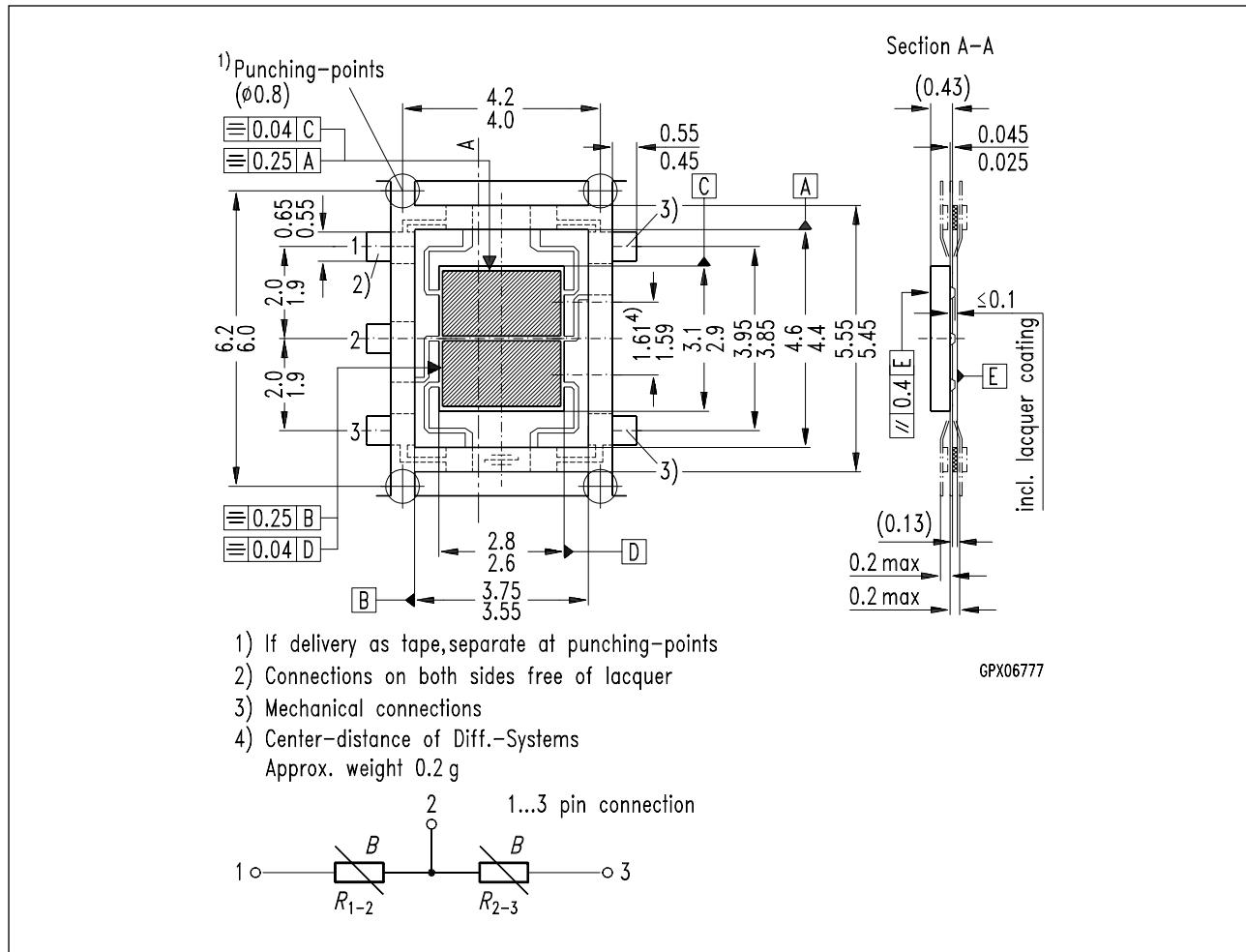


Differential Magneto Resistor

FP 412 L 100



Dimensions in mm

Features

- Accurate intercenter spacing
- High operating temperature range
- High output voltage
- Signal amplitude independent of speed
- Compact construction
- Available in strip form for automatic assembly

Typical applications

- Detection of speed
- Detection of position
- Detection of sense of rotation
- Angular encoders
- Linear position sensing

Type	Ordering Code
FP 412 L 100	Q65412-L100

The differential magneto resistor FP 412 L 100 is a magnetically variable resistor in L-type InSb/NiSb semiconductor material. The MR is glued onto a ferrite substrate and is supplied in a "MICROPACK" copper/polyimide film package. The basic resistance of each of the magneto resistors is 100 Ω . The series coupled MRs are actuated by an external magnetic field or can be biased by a permanent magnet and actuated by a soft iron target.

Maximum ratings

Parameter	Symbol	Value	Unit
Operating temperature	T_A	- 40 / + 175	°C
Storage temperature	T_{stg}	- 40 / + 185	°C
Power dissipation ¹⁾	P_{tot}	1000	mW
Supply voltage ²⁾ ($B = 0.2$ T)	V_{IN}	10	V
Thermal conductivity – attached to heatsink – in still air	$G_{th \text{ case}}$ $G_{th A}$	≥ 20 2	mW/K

Characteristics ($T_A = 25$ °C)

Basic resistance ($I \leq 1$ mA, $B = 0$ T) ³⁾	R_{01-3}	150...250	Ω
Center symmetry ⁴⁾	M	≤ 10	%
Relative resistance change $R_0 = R_{01-3}$, at $B = 0$ T $B = \pm 0.3$ T $B = \pm 1$ T	R_B/R_0	> 1.7 > 7	–
Temperature coefficient $B = 0$ T $B = \pm 0.3$ T $B = \pm 1$ T	TC_R	- 0.16 - 0.38 - 0.54	%/K %/K %/K

1) Corresponding to diagram $P_{tot} = f(T_{case})$

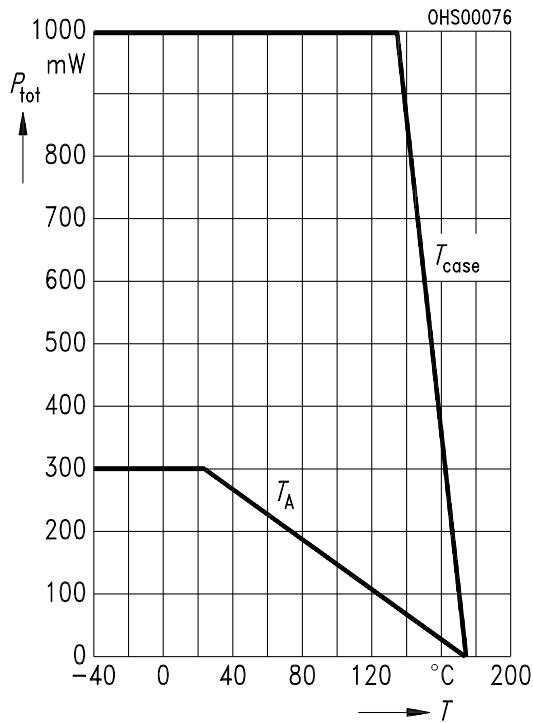
2) Corresponding to diagram $V_{IN} = f(T_{case})$

3) 1 T = 1 Tesla = 10^4 Gauss

4)
$$M = \frac{R_{01-2} - R_{02-3}}{R_{01-2}} \times 100\% \text{ for } R_{01-2} > R_{02-3}$$

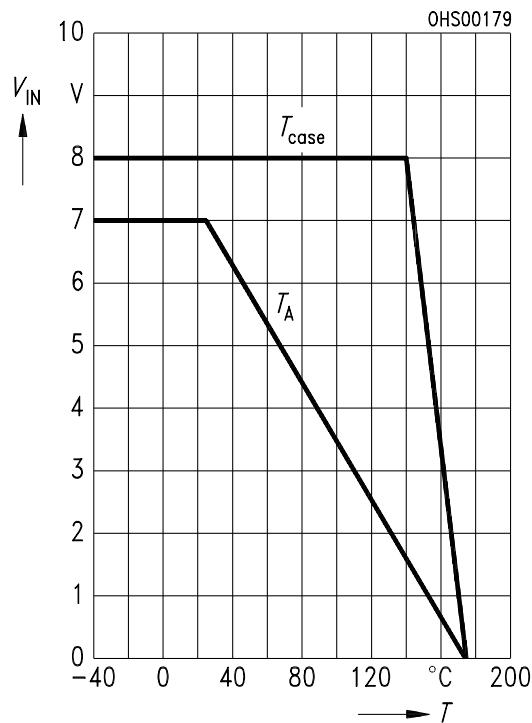
Max. power dissipation versus temperature

$$P_{\text{tot}} = f(T), T = T_{\text{case}}, T_A$$



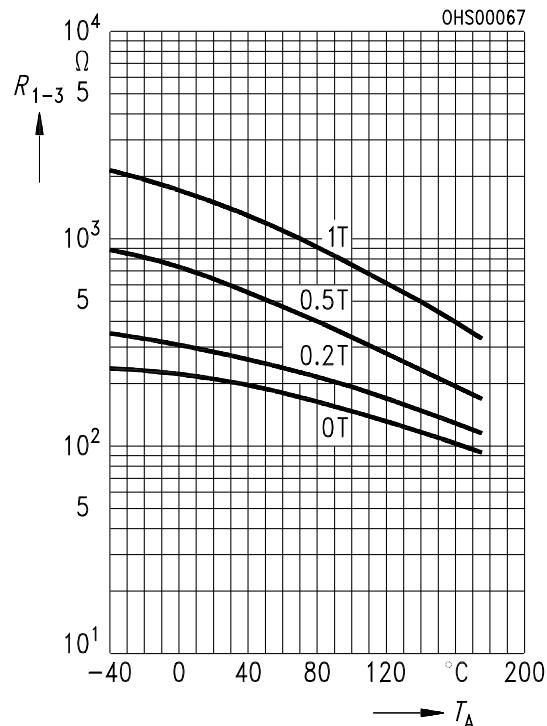
Maximum supply voltage versus temperature

$$V_{\text{IN}} = f(T), B = 0.2 \text{ T}, T = T_{\text{case}}, T_A$$



Typical MR resistance versus temperature

$$R_{1-3} = f(T_A), B = \text{Parameter}$$



Typical MR resistance versus magnetic induction B

$$R_{1-3} = f(B), T_A = 25 \text{ } ^{\circ}\text{C}$$

